MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Broduct data sheet

MSULC0524P





DFN2510-10

Features

- 60Watts peak pulse power (tp = $8/20\mu$ s)
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance (Cj=0.2pF typ. I/O to I/O)
- IEC 61000-4-2 ±20kV contact ±25kV air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 4A (8/20µs)

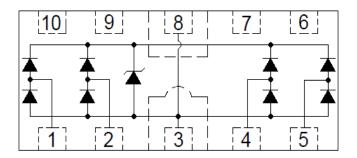
Mechanical Data

- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

Applications

- USB3.0, USB2.0, Ethernet
- HDMI 2.0, Displayport 1.3,eSATA
- Unified Display interface
- Digital Visual Interface
- High speed serial interface

Schematic & PIN Configuration



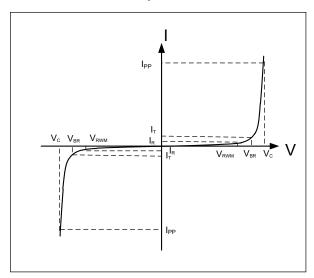


Electrical Characteristics

| Parameter | Symbol | Conditions | Min | Typical | Max | Units |
|---------------------------|-----------------|---------------------------------------------|-----|---------|------|-------|
| Reverse Stand-Off Voltage | V_{RWM} | | | | 5.0 | V |
| Reverse Breakdown Voltage | V_{BR} | I _T =1mA | 6.0 | | | V |
| Reverse Leakage Current | I _R | V _{RWM} =5V,T=25℃ | | | 1 | μΑ |
| Peak Pulse Current | I _{PP} | tp =8/20μs | | | 4 | А |
| Clamping Voltage | V _C | I _{PP} =4A,t _p =8/20μs | | | 15 | V |
| Junction Capacitance | C _j | V _R = 0V, f = 1MHz I/O to I/O | | 0.2 | 0.3 | pF |
| Junction Capacitance | | V _R = 0V, f = 1MHz I/O to GND | | 0.4 | 0.55 | рΓ |

Electrical Parameters (TA = 25°C unless otherwise noted)

| | Parameter | | |
|-----------------|----------------------------------------|--|--|
| I PP | MaximumReversePeak Pulse Current | | |
| Vc | Clamping Voltage @ IPP | | |
| VRWM | WorkingPeak Reverse Voltage | | |
| lr | Maximum Reverse Leakage Current @ VRWM | | |
| V _{BR} | Breakdown Voltage @ I⊤ | | |
| lτ | Test Current | | |
| | | | |
| | | | |



Note:.8/20 μs pulse waveform.



Typical Characteristic Curves

Fig.1 Peak Pulse Power Rating Curve

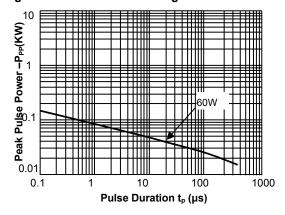


Fig.2 Pulse Derating Curve

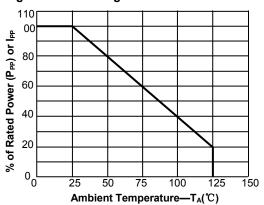


Fig.3 Pulse Waveform-8/20 μs

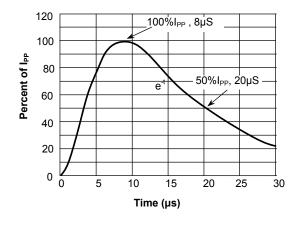
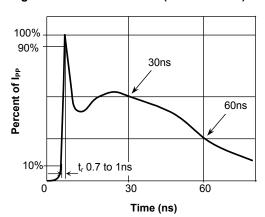


Fig.4 Pulse Waveform-ESD(IEC61000-4-2)

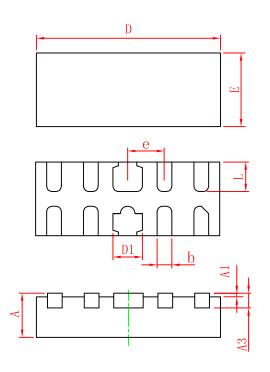




Semiconductor



PACKAGE MECHANICAL DATA



| Symbol | Dimensions in millimeters | | | | | |
|--------|---------------------------|------|------|--|--|--|
| | Min | Nom | Max | | | |
| Α | 0.45 | 0.50 | 0.55 | | | |
| A1 | - | 0.02 | 0.05 | | | |
| A3 | 0.10 | 0.15 | 0.20 | | | |
| D | 2.45 | 2.50 | 2.55 | | | |
| E | 0.95 | 1.00 | 1.05 | | | |
| D1 | 0.35 | 0.40 | 0.45 | | | |
| b | 0.15 | 0.20 | 0.25 | | | |
| е | 0.50BSC | | | | | |
| L | 0.35 | 0.40 | 0.45 | | | |

REEL SPECIFICATION

| P/N | PKG | QTY |
|------------|------------|------|
| MSULC0524P | DFN2510P10 | 3000 |



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